



THE DATASHEET OF ZTX558STZ



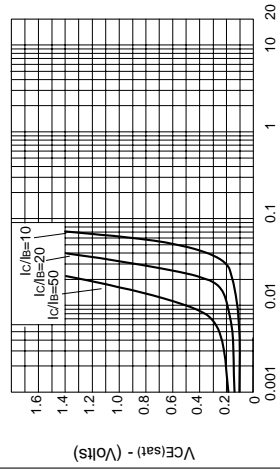
ZTX558

PNP SILICON PLANAR ME HIGH VOLTAGE TRANSIS ISSUE 1 – APRIL 94

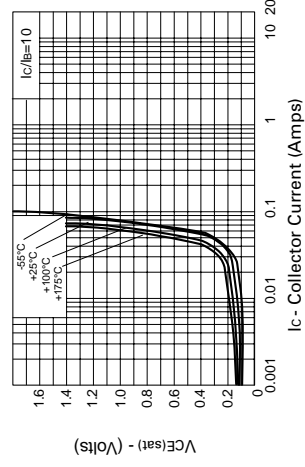
FEATURES

- * 400 Volt V_{CE0}
- * 200mA continuous current
- * $P_{tot} = 1$ Watt

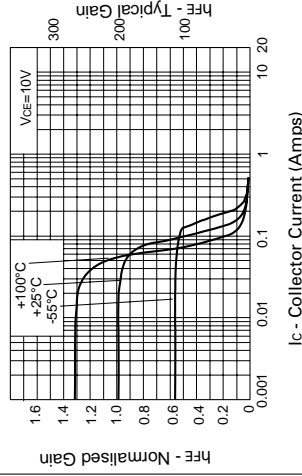
TYPICAL CHARACTERISTICS



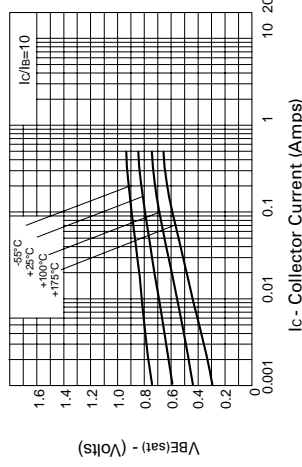
$V_{CE(sat)}$ v I_C



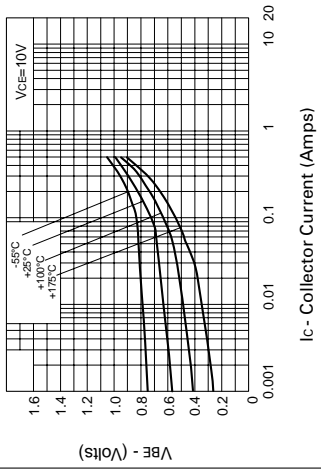
$V_{CE(sat)}$ v I_C



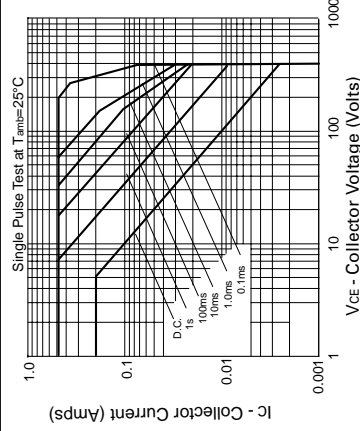
h_{FE} v I_C



$V_{BE(sat)}$ v I_C



$V_{BE(on)}$ v I_C



Safe Operating Area

ABSOLUTE MAXIMUM RATINGS

PARAMETER	MIN	MAX
Collector-Base Voltage	-4	
Collector-Emitter Voltage	-4	
Emitter-Base Voltage	-4	
Continuous Collector Current	-5	
Power Dissipation		
Operating and Storage Temperature Range		

ELECTRICAL CHARACTERISTICS

PARAMETER	SYMBOL	MIN	MAX
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	-4	
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	-4	
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	-5	
Collector Cut-Off Current	I_{CBO}		
Collector Cut-Off Current	I_{CES}		
Emitter Cut-Off Current	I_{EBO}		
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$		
Base-Emitter Saturation Voltage	$V_{BE(sat)}$		
Base-Emitter Turn On Voltage	$V_{BE(on)}$		
Static Forward Current Transfer Ratio	h_{FE}	10	150
Transition Frequency	f_T		50
Collector-Base Breakdown Voltage	C_{obo}		
Switching times	t_{on} t_{off}		

* Measured under pulsed conditions. Puls

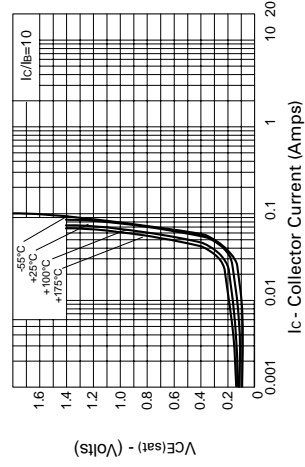
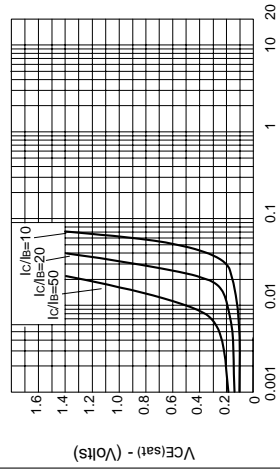
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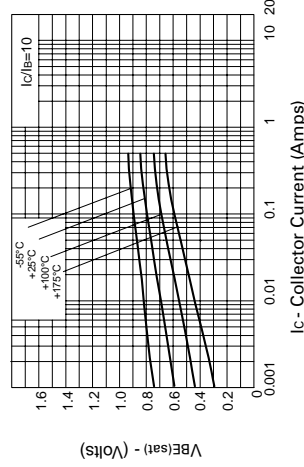
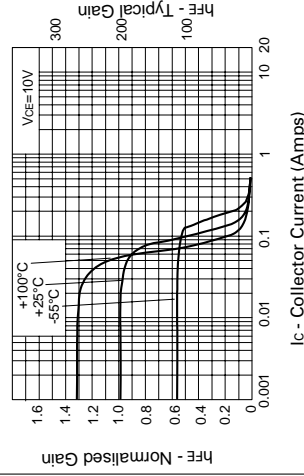
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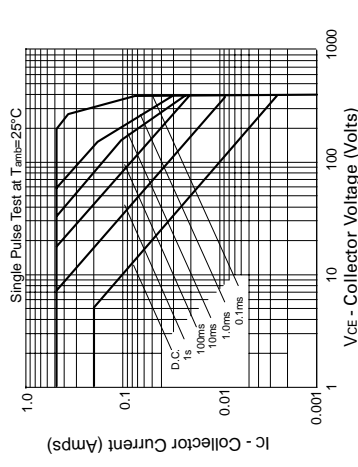
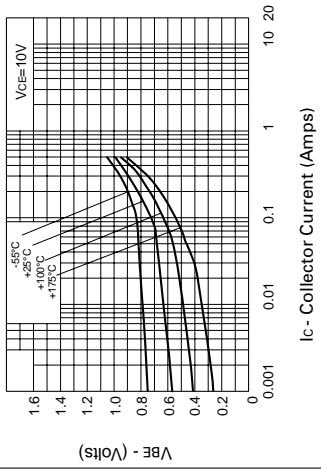
VCE(sat) v IC

VCE(sat) v IC



hFE v IC

VBE(sat) v IC



VBE(on) v IC

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